

## 1. General description

Planar passivated very sensitive gate four quadrant triac in a SOT223 (SC-73) surface-mountable plastic package intended for applications requiring direct interfacing to logic level ICs and low power gate drivers.

## 2. Features and benefits

- Direct interfacing to logic level ICs
- Direct interfacing to low power gate drive circuits
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Surface-mountable package
- Triggering in all four quadrants
- Very sensitive gate in four quadrants

## 3. Applications

- General purpose low power motor control
- Home appliances
- Industrial process control
- Low power AC Fan controllers

## 4. Quick reference data

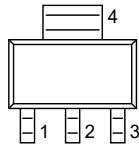
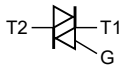
Table 1. Quick reference data

| Symbol                        | Parameter                            | Conditions   | Min | Typ | Max | Unit |
|-------------------------------|--------------------------------------|--|-----|-----|-----|------|
| $V_{DRM}$                     | repetitive peak off-state voltage    |  | -   | -   | 800 | V    |
| $I_{T(RMS)}$                  | RMS on-state current                 | full sine wave; $T_{sp} \leq 105\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a> | -   | -   | 1   | A    |
| $I_{TSM}$                     | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>  | -   | -   | 8   | A    |
|                               |                                      | full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 16.7\text{ ms}$  | -   | -   | 8.5 | A    |
| $T_j$                         | junction temperature                 |  | -   | -   | 125 | °C   |
| <b>Static characteristics</b> |                                      |  |     |     |     |      |
| $I_{GT}$                      | gate trigger current                 | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>                     | -   | -   | 3   | mA   |
|                               |                                      | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>                     | -   | -   | 3   | mA   |

| Symbol                         | Parameter                             | Conditions   | Min | Typ | Max | Unit             |
|--------------------------------|---------------------------------------|--|-----|-----|-----|------------------|
|                                |                                       | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a>  | -   | -   | 3   | mA               |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a>  | -   | -   | 5   | mA               |
| $I_H$                          | holding current                       | $V_D = 12\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>   | -   | -   | 7   | mA               |
| $V_T$                          | on-state voltage                      | $I_T = 1.4\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 12</a>  | -   | 1.3 | 1.6 | V                |
| <b>Dynamic characteristics</b> |                                       |  |     |     |     |                  |
| $dV_D/dt$                      | rate of rise of off-state voltage     | $V_{DM} = 536\text{ V}$ ; $T_j = 110\text{ }^\circ\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit; <a href="#">Fig. 14</a> | 10  | -   | -   | V/ $\mu\text{s}$ |
| $dV_{com}/dt$                  | rate of change of commutating voltage | $V_D = 400\text{ V}$ ; $T_j = 110\text{ }^\circ\text{C}$ ; $dI_{com}/dt = 0.44\text{ A/ms}$ ; gate open circuit  | 0.5 | -   | -   | V/ $\mu\text{s}$ |

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description     | Simplified outline  | Graphic symbol  |
|-----|--------|-----------------|---|---|
| 1   | T1     | main terminal 1 |  <p>SC-73 (SOT223)</p> |  <p>sym051</p> |
| 2   | T2     | main terminal 2 |   |   |
| 3   | G      | gate            |   |   |
| 4   | T2     | main terminal 2 |   |   |

## 6. Ordering information

Table 3. Ordering information

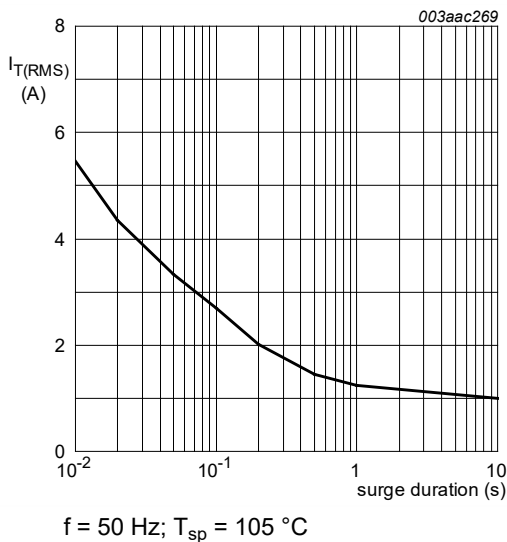
| Type number | Package |  |         |
|-------------|---------|--|---------|
|             | Name    | Description  | Version |
| Z0103NN     | SC-73   | plastic surface-mounted package with increased heatsink; 4 leads | SOT223  |

## 7. Limiting values

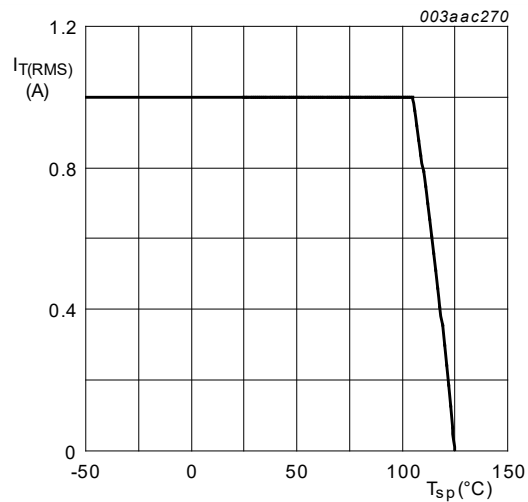
**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol       | Parameter                            | Conditions   | Min | Max  | Unit             |
|--------------|--------------------------------------|--|-----|------|------------------|
| $V_{DRM}$    | repetitive peak off-state voltage    |  | -   | 800  | V                |
| $I_{T(RMS)}$ | RMS on-state current                 | full sine wave; $T_{sp} \leq 105\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>       | -   | 1    | A                |
| $I_{TSM}$    | non-repetitive peak on-state current | full sine wave; $T_{j(\text{init})} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a> | -   | 8    | A                |
|              |                                      | full sine wave; $T_{j(\text{init})} = 25\text{ °C}$ ; $t_p = 16.7\text{ ms}$   | -   | 8.5  | A                |
| $I^2t$       | $I^2t$ for fusing                    | $t_p = 10\text{ ms}$ ; SIN   | -   | 0.32 | A <sup>2</sup> s |
| $di_T/dt$    | rate of rise of on-state current     | $I_G = 20\text{ mA}$ ; T2+ G+  | -   | 50   | A/ $\mu$ s       |
|              |                                      | $I_G = 20\text{ mA}$ ; T2+ G-  | -   | 50   | A/ $\mu$ s       |
|              |                                      | $I_G = 20\text{ mA}$ ; T2- G-  | -   | 50   | A/ $\mu$ s       |
|              |                                      | $I_G = 20\text{ mA}$ ; T2- G+  | -   | 20   | A/ $\mu$ s       |
| $I_{GM}$     | peak gate current                    |  | -   | 1    | A                |
| $P_{GM}$     | peak gate power                      |  | -   | 2    | W                |
| $P_{G(AV)}$  | average gate power                   | over any 20 ms period  | -   | 0.1  | W                |
| $T_{stg}$    | storage temperature                  |  | -40 | 150  | °C               |
| $T_j$        | junction temperature                 |  | -   | 125  | °C               |



**Fig. 1. RMS on-state current as a function of surge duration; maximum values**



**Fig. 2. RMS on-state current as a function of solder point temperature; maximum values**

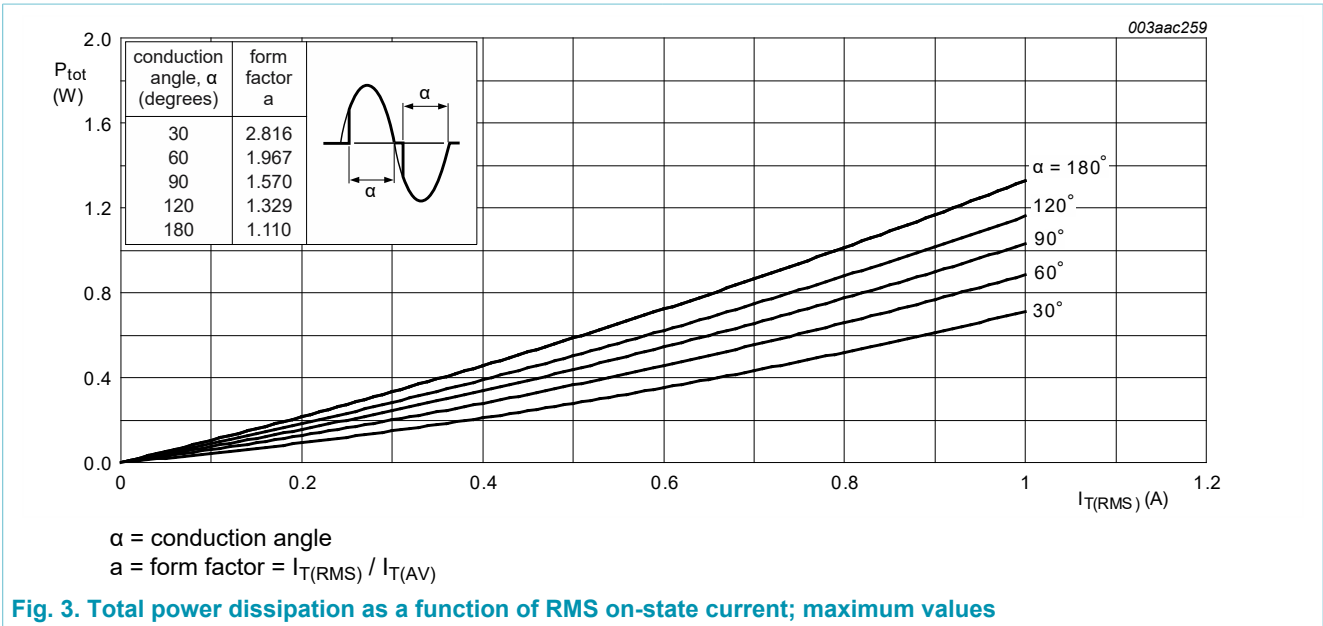


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

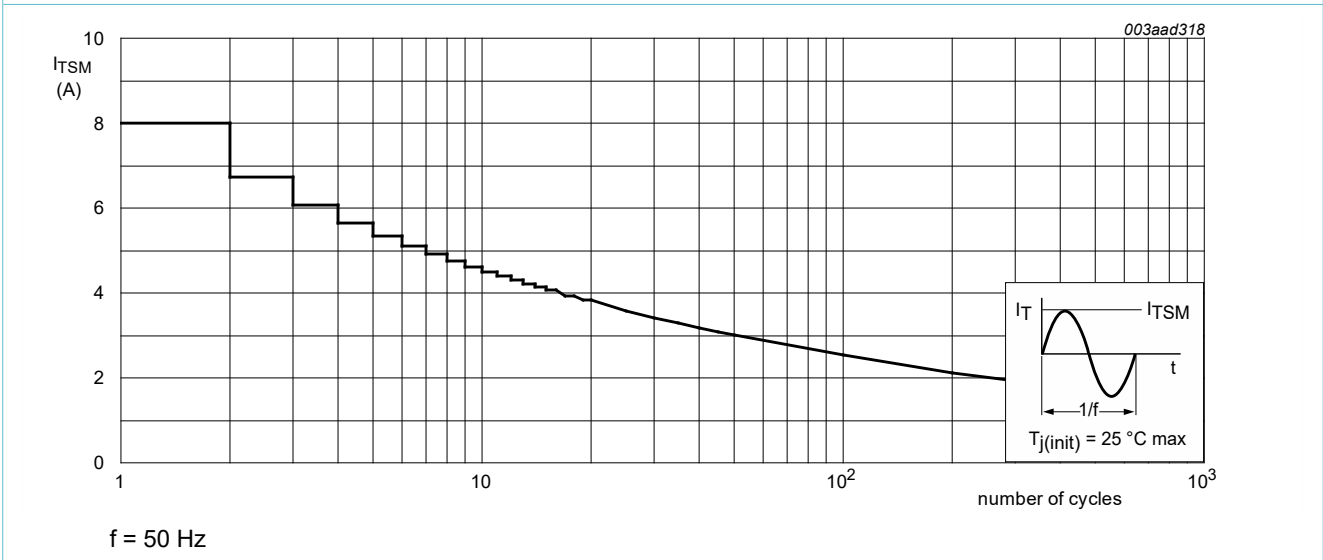
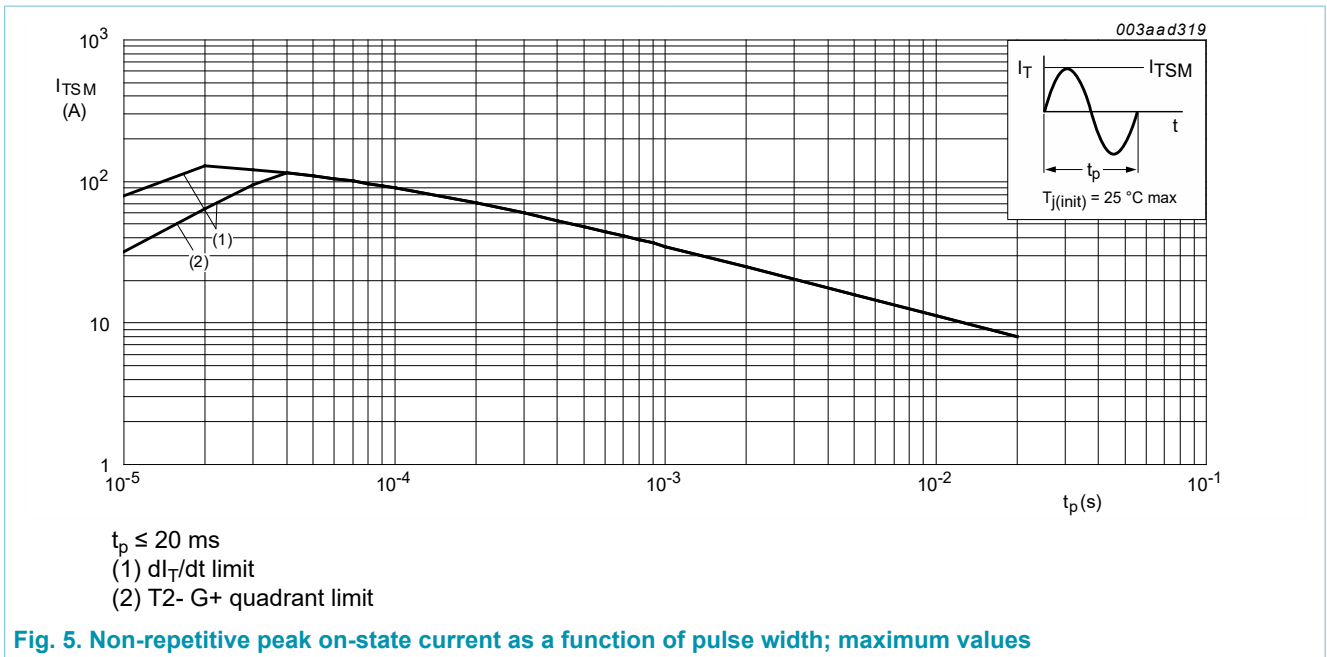


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



## 8. Thermal characteristics

Table 5. Thermal characteristics

| Symbol         | Parameter  | Conditions   | Min | Typ | Max | Unit |
|----------------|--|--|-----|-----|-----|------|
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point     | full cycle; <a href="#">Fig. 6</a>   | -   | -   | 15  | K/W  |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient free air | full cycle; printed circuit board mounted: minimum footprint; <a href="#">Fig. 7</a> | -   | 156 | -   | K/W  |
|                |  | full cycle; printed circuit board mounted: pad area; <a href="#">Fig. 8</a>          | -   | 70  | -   | K/W  |

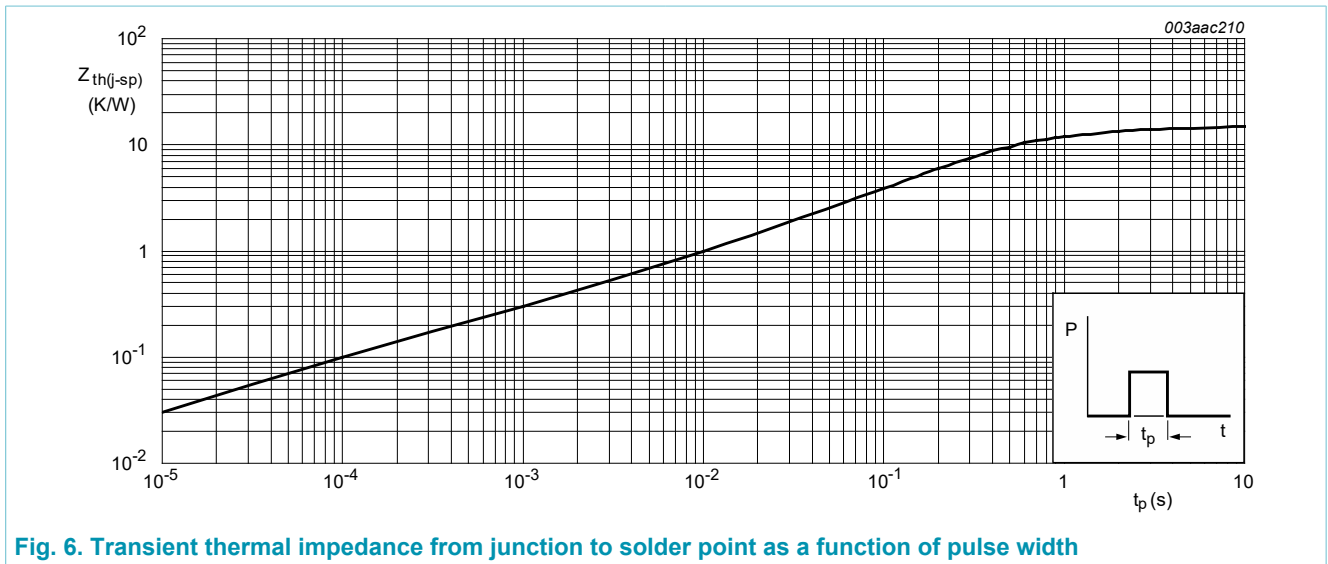
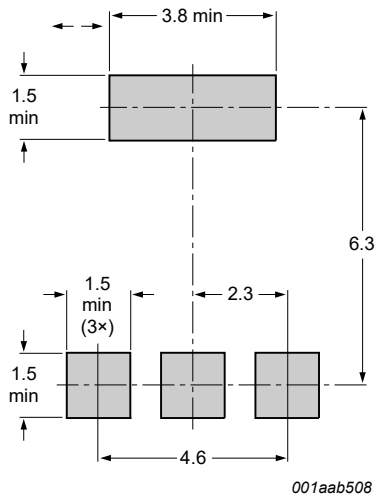
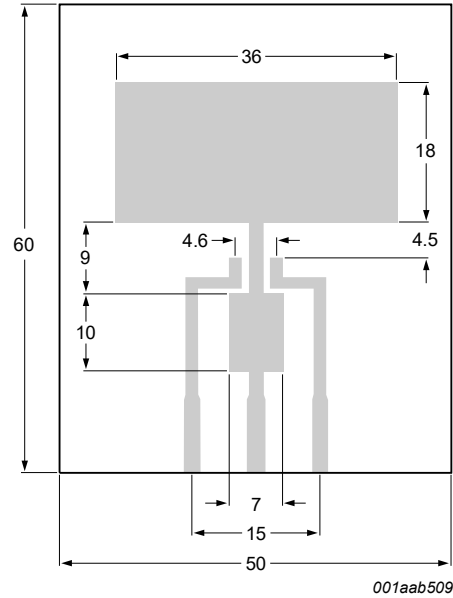


Fig. 6. Transient thermal impedance from junction to solder point as a function of pulse width



All dimensions are in mm

**Fig. 7. Minimum footprint SOT223**



All dimensions are in mm

Printed circuit board:

FR4 epoxy glass (1.6 mm thick), copper laminate (35 um thick)

**Fig. 8. Printed circuit board pad area: SOT223**

## 9. Characteristics

Table 6. Characteristics

| Symbol                         | Parameter                             | Conditions   | Min | Typ | Max | Unit       |
|--------------------------------|---------------------------------------|--|-----|-----|-----|------------|
| <b>Static characteristics</b>  |                                       |  |     |     |     |            |
| $I_{GT}$                       | gate trigger current                  | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>  | -   | -   | 3   | mA         |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>  | -   | -   | 3   | mA         |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>  | -   | -   | 3   | mA         |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G+;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>  | -   | -   | 5   | mA         |
| $I_L$                          | latching current                      | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G+;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 10</a>   | -   | -   | 7   | mA         |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G-;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 10</a>   | -   | -   | 15  | mA         |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 10</a>   | -   | -   | 7   | mA         |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G+;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 10</a>   | -   | -   | 7   | mA         |
| $I_H$                          | holding current                       | $V_D = 12\text{ V}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 11</a>   | -   | -   | 7   | mA         |
| $V_T$                          | on-state voltage                      | $I_T = 1.4\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 12</a>  | -   | 1.3 | 1.6 | V          |
| $V_{GT}$                       | gate trigger voltage                  | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ °C}$ ;<br><a href="#">Fig. 13</a>   | -   | -   | 1   | V          |
|                                |                                       | $V_D = 800\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 125\text{ °C}$ ;<br><a href="#">Fig. 13</a>   | 0.2 | -   | -   | V          |
| $I_D$                          | off-state current                     | $V_D = 800\text{ V}$ ; $T_j = 125\text{ °C}$   | -   | -   | 0.5 | mA         |
| <b>Dynamic characteristics</b> |                                       |  |     |     |     |            |
| $dV_D/dt$                      | rate of rise of off-state voltage     | $V_{DM} = 536\text{ V}$ ; $T_j = 110\text{ °C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit; <a href="#">Fig. 14</a> | 10  | -   | -   | V/ $\mu$ s |
| $dV_{com}/dt$                  | rate of change of commutating voltage | $V_D = 400\text{ V}$ ; $T_j = 110\text{ °C}$ ; $dI_{com}/dt = 0.44\text{ A/ms}$ ; gate open circuit  | 0.5 | -   | -   | V/ $\mu$ s |



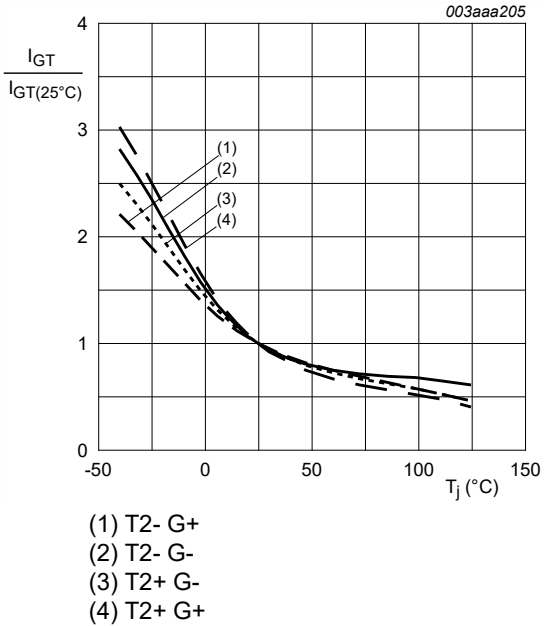


Fig. 9. Normalized gate trigger current as a function of junction temperature

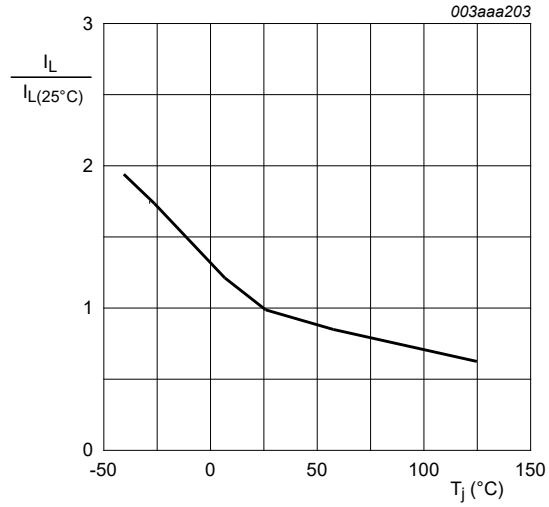


Fig. 10. Normalized latching current as a function of junction temperature

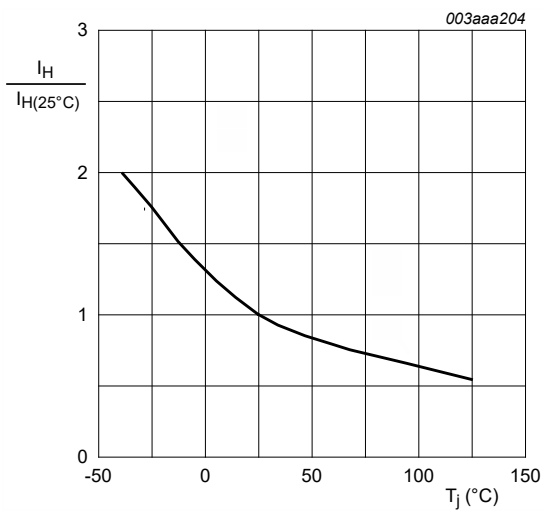
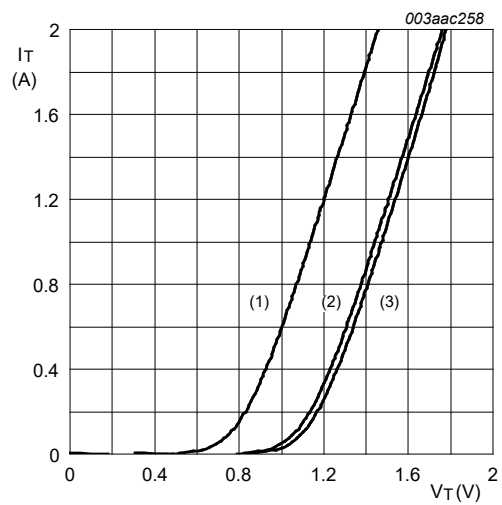


Fig. 11. Normalized holding current as a function of junction temperature



$V_o = 1.13 \text{ V}$   
 $R_s = 0.31 \Omega$   
 (1)  $T_j = 125 \text{ }^\circ\text{C}$ ; typical values  
 (2)  $T_j = 125 \text{ }^\circ\text{C}$ ; maximum values  
 (3)  $T_j = 25 \text{ }^\circ\text{C}$ ; maximum values

Fig. 12. On-state current as a function of on-state voltage

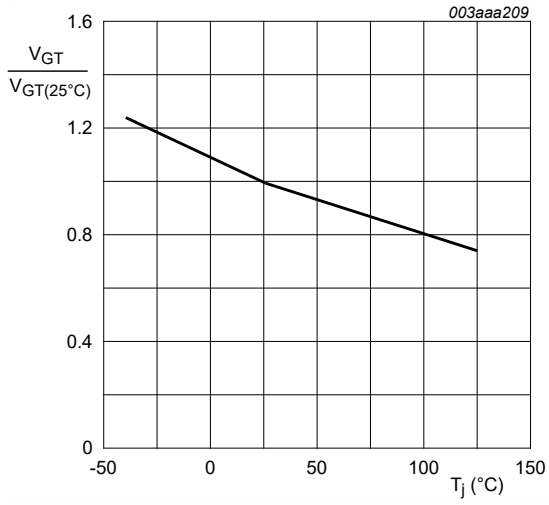
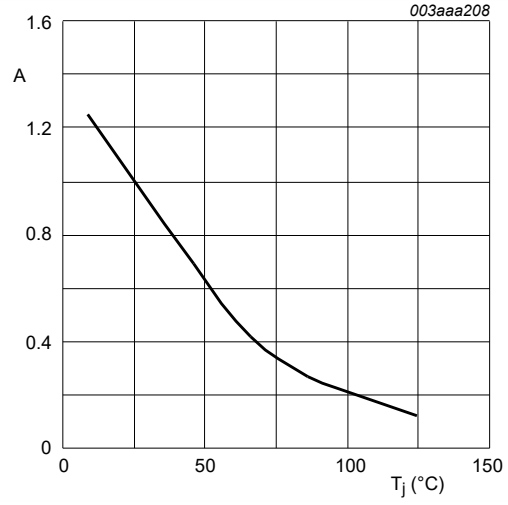


Fig. 13. Normalized gate trigger voltage as a function of junction temperature



$$A = \frac{dV_D(T_j \text{ } ^\circ\text{C}) / dt}{dV_D(25 \text{ } ^\circ\text{C}) / dt}$$

Fig. 14. Normalized critical rate of rise of off-state voltage as a function of junction temperature; typical values

### 10. Package outline

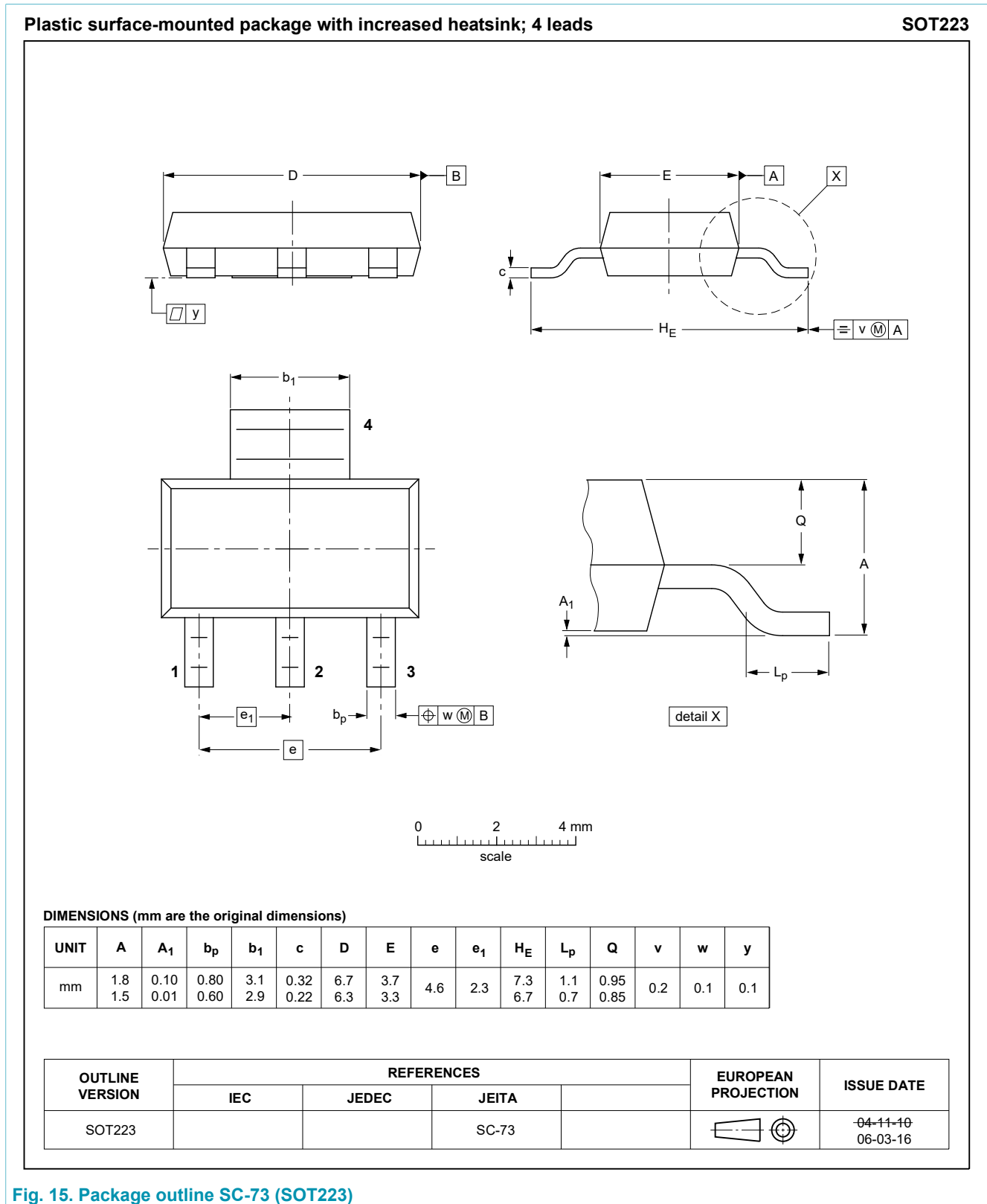


Fig. 15. Package outline SC-73 (SOT223)

## 11. Legal information

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| Document status [1][2]         | Product status [3] | Definition  |
|--------------------------------|--------------------|---|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
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- [2] The term 'short data sheet' is explained in section "Definitions".
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Date of release: 15 September 2018

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- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



#### Как с нами связаться

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